

GP2M010A060H

GP2M010A060H Information

www.heisomy.com		GP2M010A060H Global Power Technologies Group Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single MOSFET N-CH 600V 10A TO220	
	Package	TO-220-3 For the pricing/inventory/lead time, please contact us	
For Reference Only		Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



GP2M010A060H Specifications

Manufacturer Part Number	GP2M010A060H
Manufacturer	Global Power Technologies Group
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-220-3
Series	-
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	600V
Current - Continuous Drain (Id) @ 25°C	10A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	10V
Vgs(th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	35nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	1660pF @ 25V
Vgs (Max)	±30V
FET Feature	-
Power Dissipation (Max)	198W (Tc)
Rds On (Max) @ Id, Vgs	700 mOhm @ 5A, 10V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Through Hole
Supplier Device Package	TO-220
Package / Case	TO-220-3
	Report errors?

GP2M010A060H Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE BUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

GP2M010A060H Payment Methods





If you have any question about GP2M010A060H, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com